REVISION HISTORY

REVISION	DESCRIPTION	Draft Date
Preliminary Rev. 0.1	Original.	Apr. 15, 2003

FEATURES

- Fast access time : 55/70/100ns
- CMOS low power operating
  Operating current : 30/20/16 (Icc) (TYP.)
  Standby current : 20uA (TYP.) L-version
  2uA (TYP.) LL-version
- Single 2.7V~3.6V power supply
- Operation temperature:
  Industrial : -40℃~85℃
- All TTL compatible inputs and outputs
- Fully static operation
- Three state outputs
- Data retention voltage:1.5V (min.)
- Data byte control : $\overline{LB}$ (I/O1~I/O8)
  $\overline{UB}$ (I/O9~I/O16)
- Package : 48-pin 12mmX20mm TSOP-I
  48-ball 6mm × 8mm TFBGA

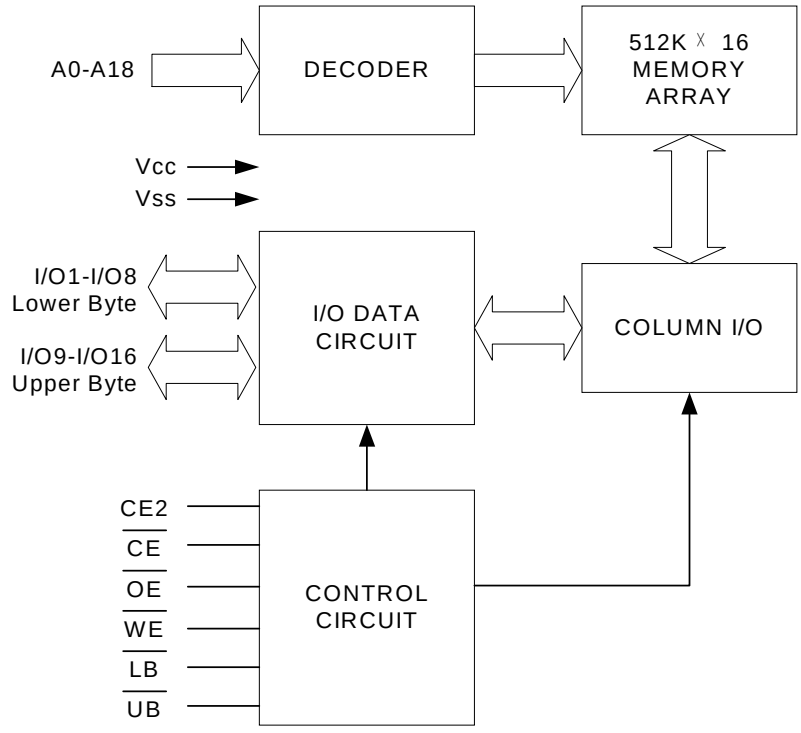
GENERAL DESCRIPTION

The UT62L51316(I) is a 8,388,608-bit low power CMOS static random access memory organized as 524,288 words by 16 bits.

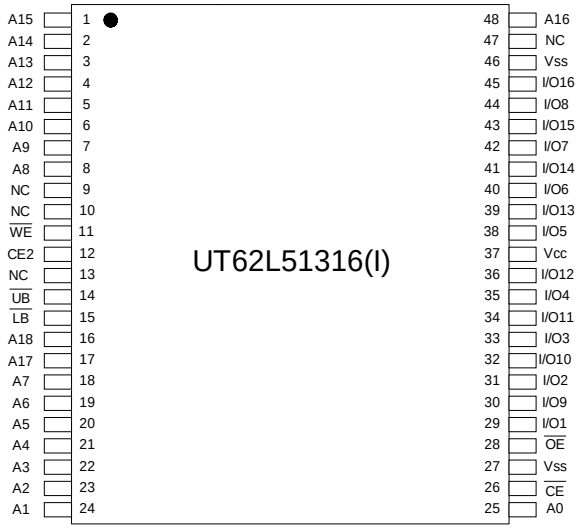
The UT62L51316(I) operates from a single 2.7V ~ 3.6V power supply and all inputs and outputs are fully TTL compatible.

The UT62L51316(I) is designed for low power system applications. It is particularly well suited for use in high-density low power system applications.

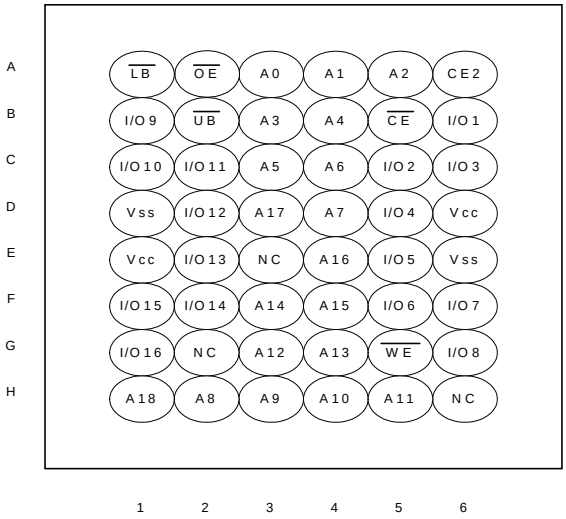
FUNCTIONAL BLOCK DIAGRAM



PIN CONFIGURATION



TSOP-I



TFBGA

PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0 - A18	Address Inputs
I/O1 - I/O16	Data Inputs/Outputs
$\overline{CE}$, CE2	Chip Enable Input
$\overline{WE}$	Write Enable Input
$\overline{OE}$	Output Enable Input
$\overline{LB}$	Lower-byte Control
$\overline{UB}$	Upper-byte Control
V_{CC}	Power Supply
V_{SS}	Ground
NC	No Connection

TRUTH TABLE

MODE	$\overline{CE}$	CE2	$\overline{OE}$	$\overline{WE}$	$\overline{LB}$	$\overline{UB}$	I/O OPERATION		SUPPLY CURRENT
							I/O1-I/O8	I/O9-I/O16	
Standby	H	X	X	X	X	X	High – Z	High – Z	I_{SB}, I_{SB1}
	X	L	X	X	X	X	High – Z	High – Z	
	X	X	X	X	H	H	High – Z	High – Z	
Output Disable	L	H	H	H	L	X	High – Z	High – Z	I_{CC},I_{CC1}, I_{CC2}
	L	H	H	H	X	L	High – Z	High – Z	
Read	L	H	L	H	L	H	D_{OUT}	High – Z	I_{CC},I_{CC1}, I_{CC2}
	L	H	L	H	H	L	High – Z	D_{OUT}	
	L	H	L	H	L	L	D_{OUT}	D_{OUT}	
Write	L	H	X	L	L	H	D_{IN}	High – Z	I_{CC},I_{CC1}, I_{CC2}
	L	H	X	L	H	L	High – Z	D_{IN}	
	L	H	X	L	L	L	D_{IN}	D_{IN}	

Note: H = V_{IH}, L=V_{IL}, X = Don't care.

ABSOLUTE MAXIMUM RATINGS*

PARAMETER		SYMBOL	RATING	UNIT
Terminal Voltage with Respect to V_{SS}		V_{TERM}	-0.5 to 4.6	V
Operating Temperature	Industrial	T_A	-40 to 85	°C
Storage Temperature		T_{STG}	-65 to 150	°C
Power Dissipation		P_D	1	W
DC Output Current		I_{OUT}	50	mA
Soldering Temperature (under 10 secs)		Tsolder	260	°C

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (V_{CC} = 2.7V~3.6V, T_A = -40°C to 85°C(I))

PARAMETER	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Power Voltage	V_{CC}			2.7	3.0	3.6	V
Input High Voltage	V_{IH} *1			2.2	-	V_{CC}+0.3	V
Input Low Voltage	V_{IL} *2			-0.2	-	0.6	V
Input Leakage Current	I_{LI}	$V_{SS} \leqq V_{IN} \leqq V_{CC}$		- 1	-	1	µA
Output Leakage Current	I_{LO}	$V_{SS} \leqq V_{I/O} \leqq V_{CC;}$ Output Disable		- 1	-	1	µA
Output High Voltage	V_{OH}	I_{OH}= -1mA		2.2	2.7	-	V
Output Low Voltage	V_{OL}	I_{OL}= 2.1mA		-	-	0.4	V
Operating Power Supply Current	I_{CC}	Cycle time=min, 100%duty I/O=0mA, $\overline{CE}$=V_{IL}, CE2=V_{IH}, $\overline{LB}$ or $\overline{UB}$=V_{IL}	55	-	30	40	mA
			70	-	20	30	mA
			100	-	16	25	mA
Average Operation Current	I_{CC1}	Cycle time=1µs, 100% duty, $I_{I/O}$=0mA, $\overline{CE} \leqq$0.2V,CE2$\geqq V_{CC}$-0.2V, $\overline{LB}$ or $\overline{UB} \leqq$0.2V, other pins at 0.2V or Vcc-0.2V		-	4	5	mA
	I_{CC2}	Cycle time=500ns, 100% duty, $I_{I/O}$=0mA, $\overline{CE} \leqq$0.2V,CE2$\geqq V_{CC}$-0.2V, $\overline{LB}$ or $\overline{UB} \leqq$0.2V, other pins at 0.2V or Vcc-0.2V		-	8	10	mA
Standby Current (TTL)	I_{SB}	$\overline{CE}$=V_{IH}, or CE2=V_{IL}, or $\overline{LB}$ = $\overline{UB}$ =V_{IH}		-	0.3	0.5	mA
Standby Current (CMOS)	I_{SB1}	$\overline{CE} \geqq V_{CC}$-0.2V, or CE2$\leqq$0.2V, or $\overline{LB}$ = $\overline{UB}$ =V_{CC}-0.2V,	-L	-	20	80	µA
			-LL	-	2	20	µA

Notes:
1. Overshoot : Vcc+2.0v for pulse width less than 10ns.
2. Undershoot : Vss-2.0v for pulse width less than 10ns.
3. Overshoot and Undershoot are sampled, not 100% tested.

CAPACITANCE (T_A=25℃, f=1.0MHz)

PARAMETER	SYMBOL	MIN.	MAX	UNIT
Input Capacitance	C_{IN}	-	6	pF
Input/Output Capacitance	$C_{I/O}$	-	8	pF

Note : These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

Input Pulse Levels	$0.1V_{CC}$ to $0.9V_{CC}$
Input Rise and Fall Times	5ns
Input and Output Timing Reference Levels	1.5V
Output Load	C_L = 30pF+1 TTL, I_{OH}/I_{OL} = -1mA/2.1mA

AC ELECTRICAL CHARACTERISTICS (V_{CC} = 2.7V~3.6V , T_A = -40℃ to 85℃(I))

(1) READ CYCLE

PARAMETER	SYMBOL	UT62L51316(I)-55		UT62L51316(I)-70		UT62L51316(I)-100		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	t_{RC}	55	-	70	-	100	-	ns
Address Access Time	t_{AA}	-	55	-	70	-	100	ns
Chip Enable Access Time	t_{ACE}	-	55	-	70	-	100	ns
Output Enable Access Time	t_{OE}	-	30	-	35	-	50	ns
Chip Enable to Output in Low Z	t_{CLZ}*	10	-	10	-	10	-	ns
Output Enable to Output in Low Z	t_{OLZ}*	5	-	5	-	5	-	ns
Chip Disable to Output in High Z	t_{CHZ}*	-	20	-	25	-	30	ns
Output Disable to Output in High Z	t_{OHZ}*	-	20	-	25	-	30	ns
Output Hold from Address Change	t_{OH}	10	-	10	-	10	-	ns
$\overline{LB}$, $\overline{UB}$ Access Time	t_{BA}	-	55	-	70	-	100	ns
$\overline{LB}$, $\overline{UB}$ to High-Z Output	t_{BHZ}*	-	20	-	25	-	30	ns
$\overline{LB}$, $\overline{UB}$ to Low-Z Output	t_{BLZ}*	10	-	10	-	10	-	ns

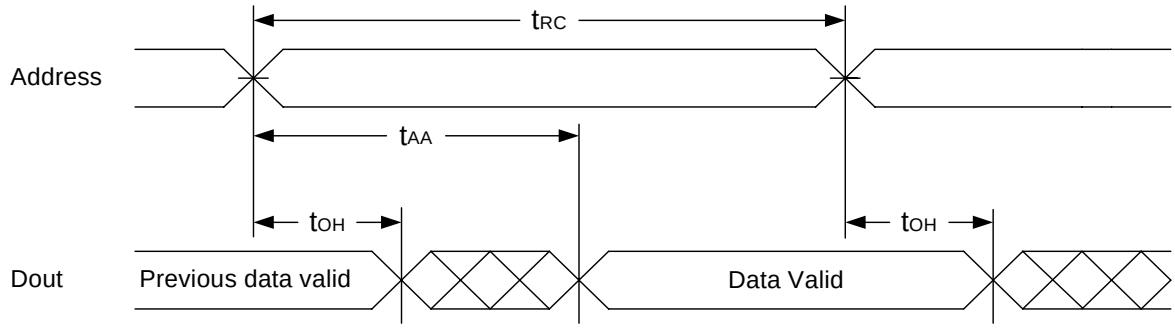
(2) WRITE CYCLE

PARAMETER	SYMBOL	UT62L51316(I)-55		UT62L51316(I)-70		UT62L51316(I)-100		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Write Cycle Time	t_{WC}	55	-	70	-	100	-	ns
Address Valid to End of Write	t_{AW}	50	-	60	-	80	-	ns
Chip Enable to End of Write	t_{CW}	50	-	60	-	80	-	ns
Address Set-up Time	t_{AS}	0	-	0	-	0	-	ns
Write Pulse Width	t_{WP}	45	-	55	-	70	-	ns
Write Recovery Time	t_{WR}	0	-	0	-	0	-	ns
Data to Write Time Overlap	t_{DW}	25	-	30	-	40	-	ns
Data Hold from End of Write Time	t_{DH}	0	-	0	-	0	-	ns
Output Active from End of Write	t_{OW}*	5	-	5	-	5	-	ns
Write to Output in High Z	t_{WHZ}*	-	20	-	25	-	30	ns
$\overline{LB}$, $\overline{UB}$ Valid to End of Write	t_{BW}	50	-	60	-	80	-	ns

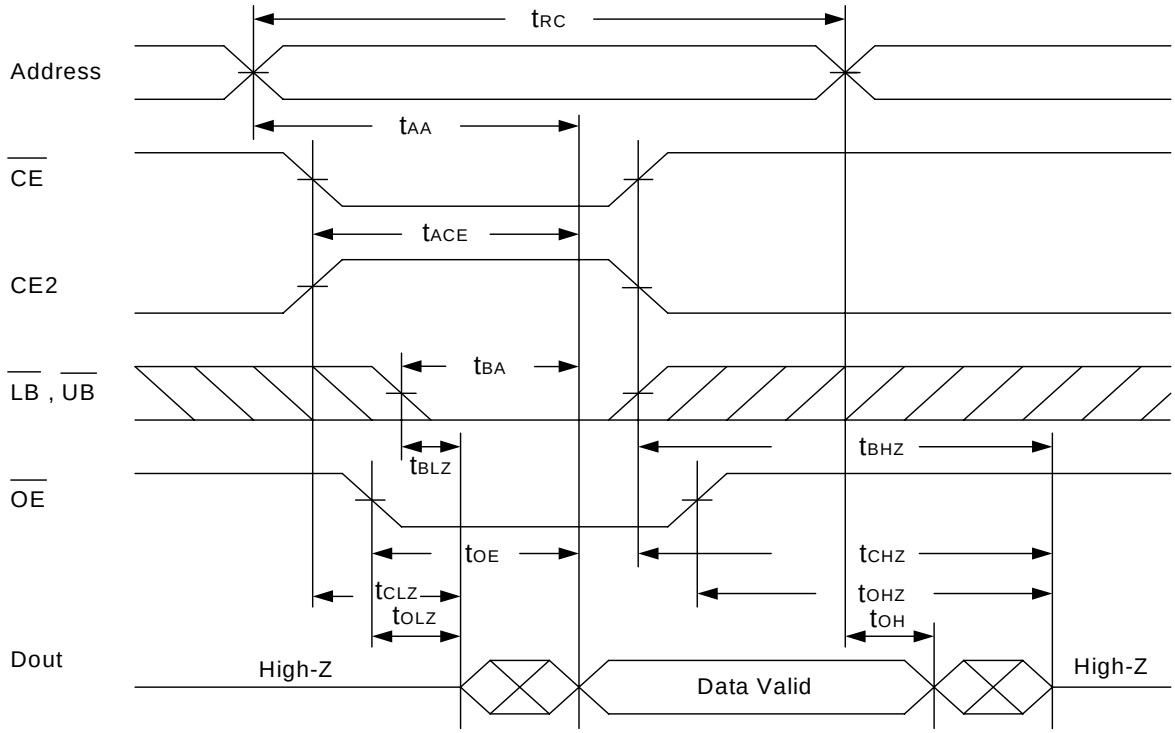
* These parameters are guaranteed by device characterization, but not production tested.

TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2)



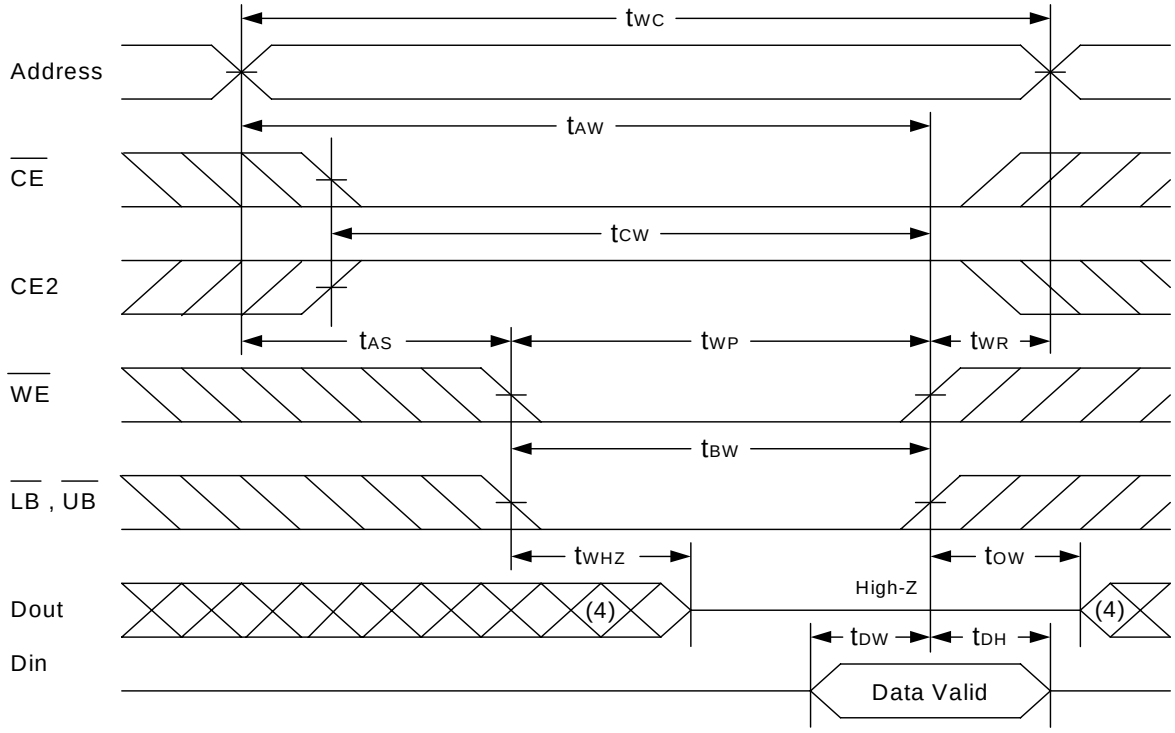
READ CYCLE 2 ($\overline{CE}$ and CE2 and $\overline{OE}$ Controlled) (1,3,4,5)



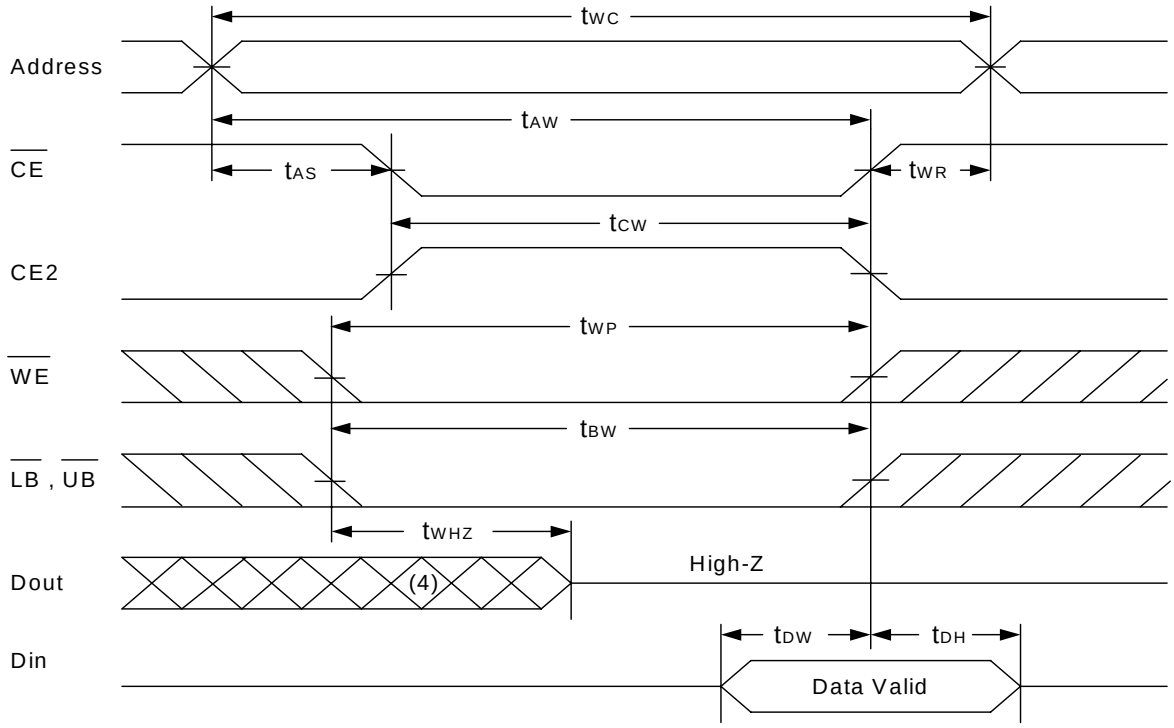
Notes :

1. $\overline{WE}$ is high for read cycle.
2. Device is continuously selected $\overline{OE}$ =low, $\overline{CE}$ =low, CE2=high, $\overline{LB}$ or $\overline{UB}$ =low.
3. Address must be valid prior to or coincident with $\overline{CE}$ =low, CE2=high, $\overline{LB}$ or $\overline{UB}$ =low transition; otherwise t_{AA} is the limiting parameter.
4. t_{CLZ}, t_{BLZ}, t_{OLZ}, t_{CHZ}, t_{BHZ} and t_{OHZ} are specified with C_L=5pF. Transition is measured±500mV from steady state.
5. At any given temperature and voltage condition, t_{CHZ} is less than t_{CLZ}, t_{BHZ} is less than t_{BLZ}, t_{OHZ} is less than t_{OLZ}.

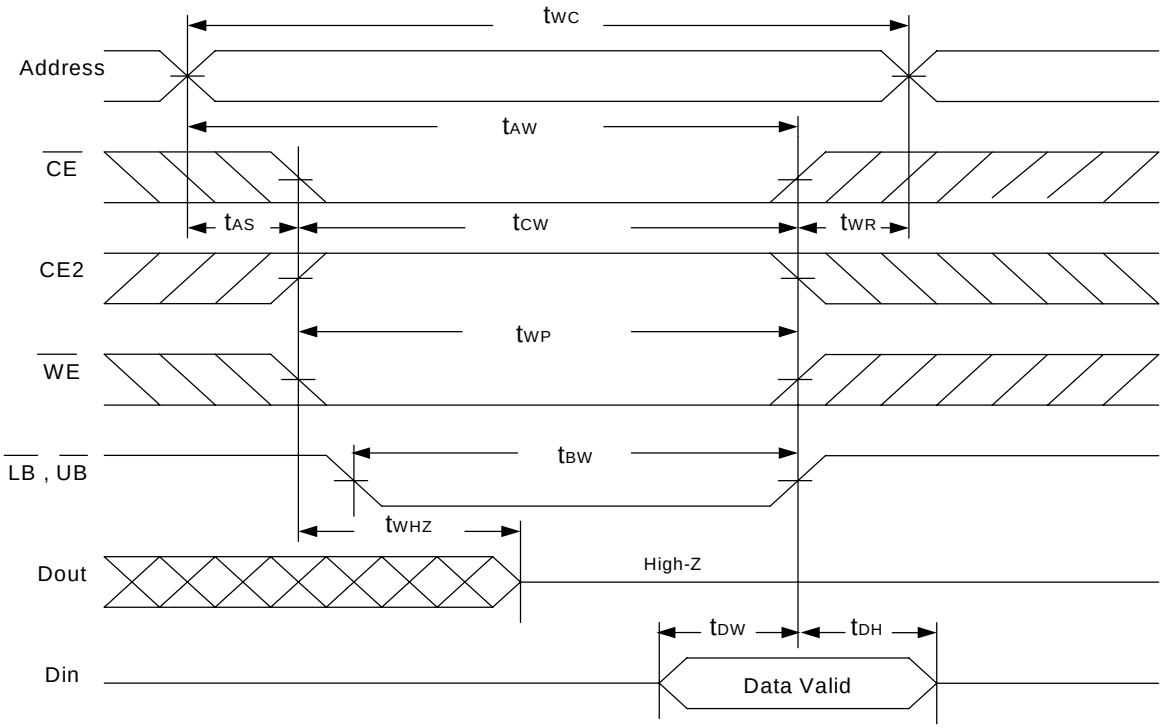
WRITE CYCLE 1 ($\overline{WE}$ Controlled) (1,2,3,5,6)



WRITE CYCLE 2 ($\overline{CE}$ and CE2 Controlled) (1,2,5,6)



WRITE CYCLE 3 ($\overline{LB}$, $\overline{UB}$ Controlled) (1,2,5,6)



Notes :

1. $\overline{WE}$, $\overline{CE}$, $\overline{LB}$, $\overline{UB}$ must be high or CE2 must be low during all address transitions.
2. A write occurs during the overlap of a low $\overline{CE}$, high CE2, low $\overline{WE}$, $\overline{LB}$ or $\overline{UB}$ =low.
3. During a $\overline{WE}$ controlled write cycle with $\overline{OE}$ low, t_{WP} must be greater than $t_{WHZ}+t_{DW}$ to allow the drivers to turn off and data to be placed on the bus.
4. During this period, I/O pins are in the output state, and input signals must not be applied.
5. If the $\overline{CE}$, $\overline{LB}$, $\overline{UB}$ low transition and CE2 high transition occurs simultaneously with or after $\overline{WE}$ low transition, the outputs remain in a high impedance state.
6. t_{OW} and t_{WHZ} are specified with C_L = 5pF. Transition is measured ±500mV from steady state.

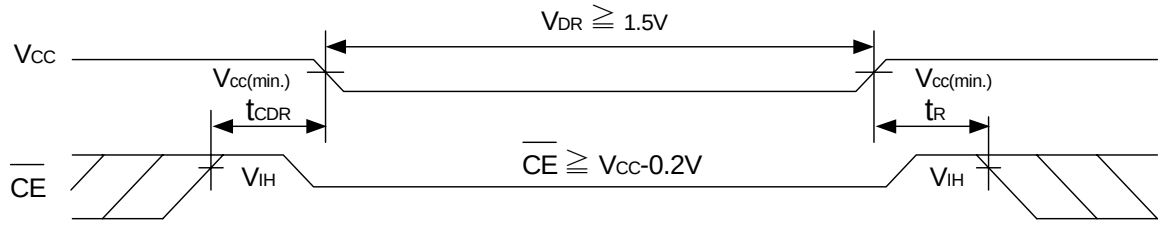
DATA RETENTION CHARACTERISTICS (T_A = -40℃ to 85℃(I))

PARAMETER	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Vcc for Data Retention	V_{DR}	$\overline{CE} \geqq V_{CC}$-0.2V or CE2≦0.2V or $\overline{LB} = \overline{UB} \geqq V_{CC}$-0.2V		1.5	-	3.6	V
Data Retention Current	I_{DR}	Vcc=1.5V	- L	-	10	80	µA
		$\overline{CE} \geqq V_{CC}$-0.2V, CE2≦0.2V, $\overline{LB} = \overline{UB} \geqq V_{CC}$-0.2V	- LL	-	1	8	µA
Chip Disable to Data Retention Time	t_{CDR}	See Data Retention Waveforms (below)		0	-	-	ns
Recovery Time	t_R			t_{RC}*	-	-	ns

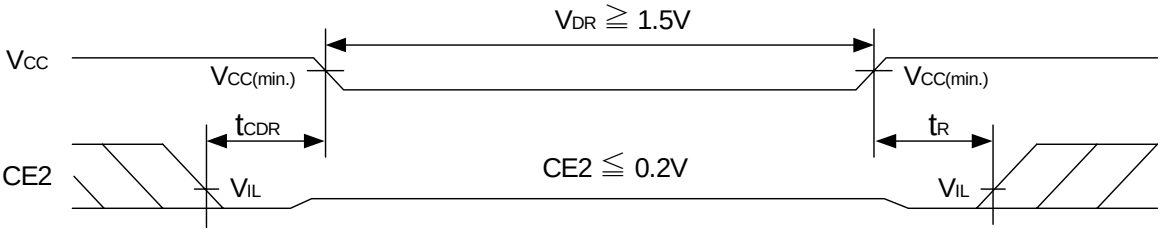
t_{RC}* = Ready Cycle Time

DATA RETENTION WAVEFORM

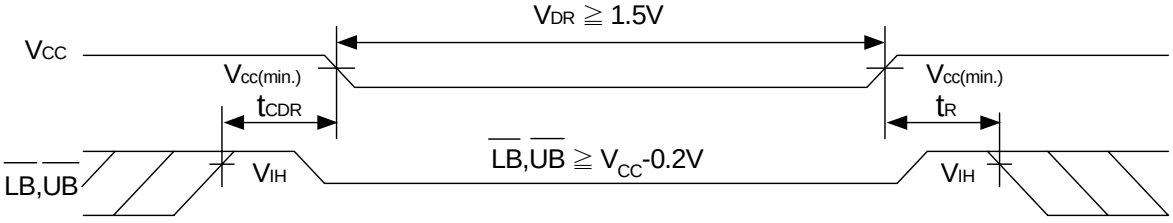
Low Vcc Data Retention Waveform (1) ($\overline{CE}$ controlled)



Low Vcc Data Retention Waveform (2) (CE2 controlled)

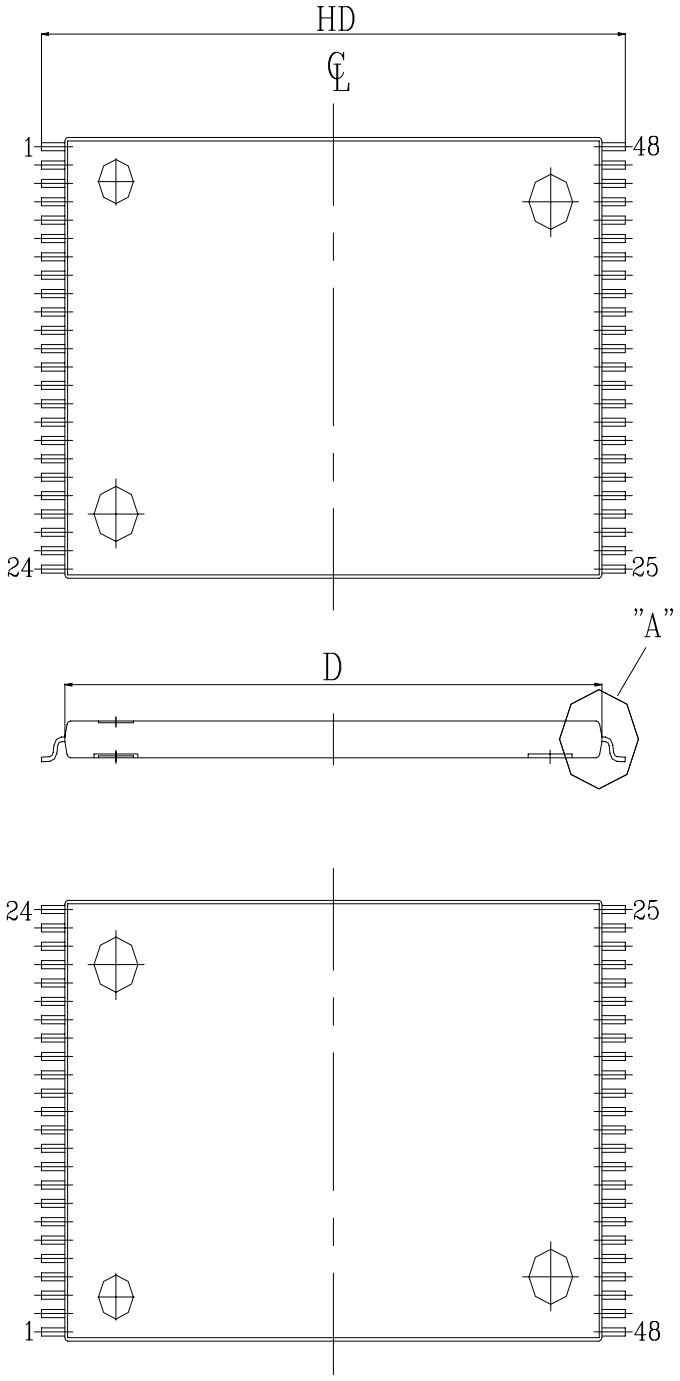


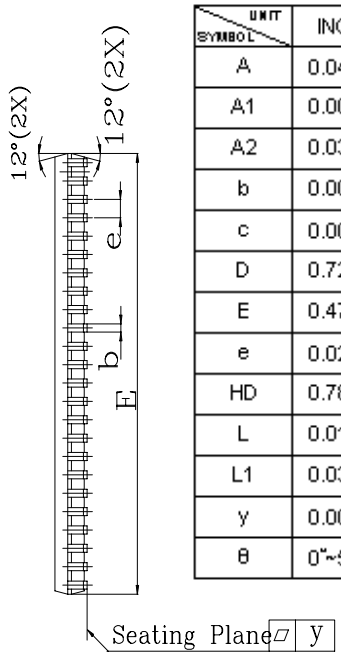
Low Vcc Data Retention Waveform (3) ($\overline{LB}$, $\overline{UB}$ controlled)



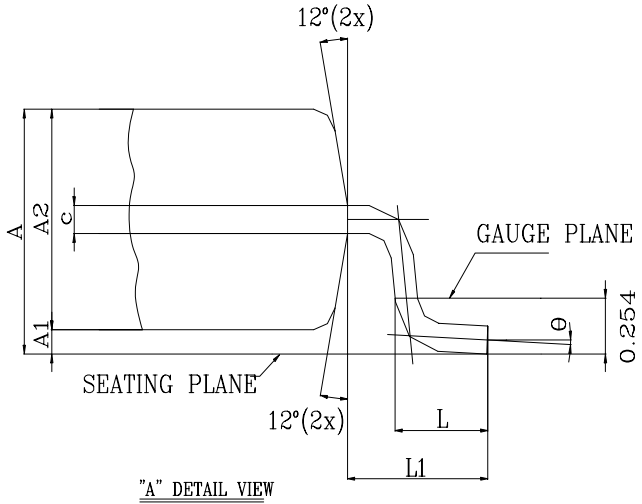
PACKAGE OUTLINE DIMENSION

48 pin 12mm x 20mm TSOP-I Package Outline Dimension

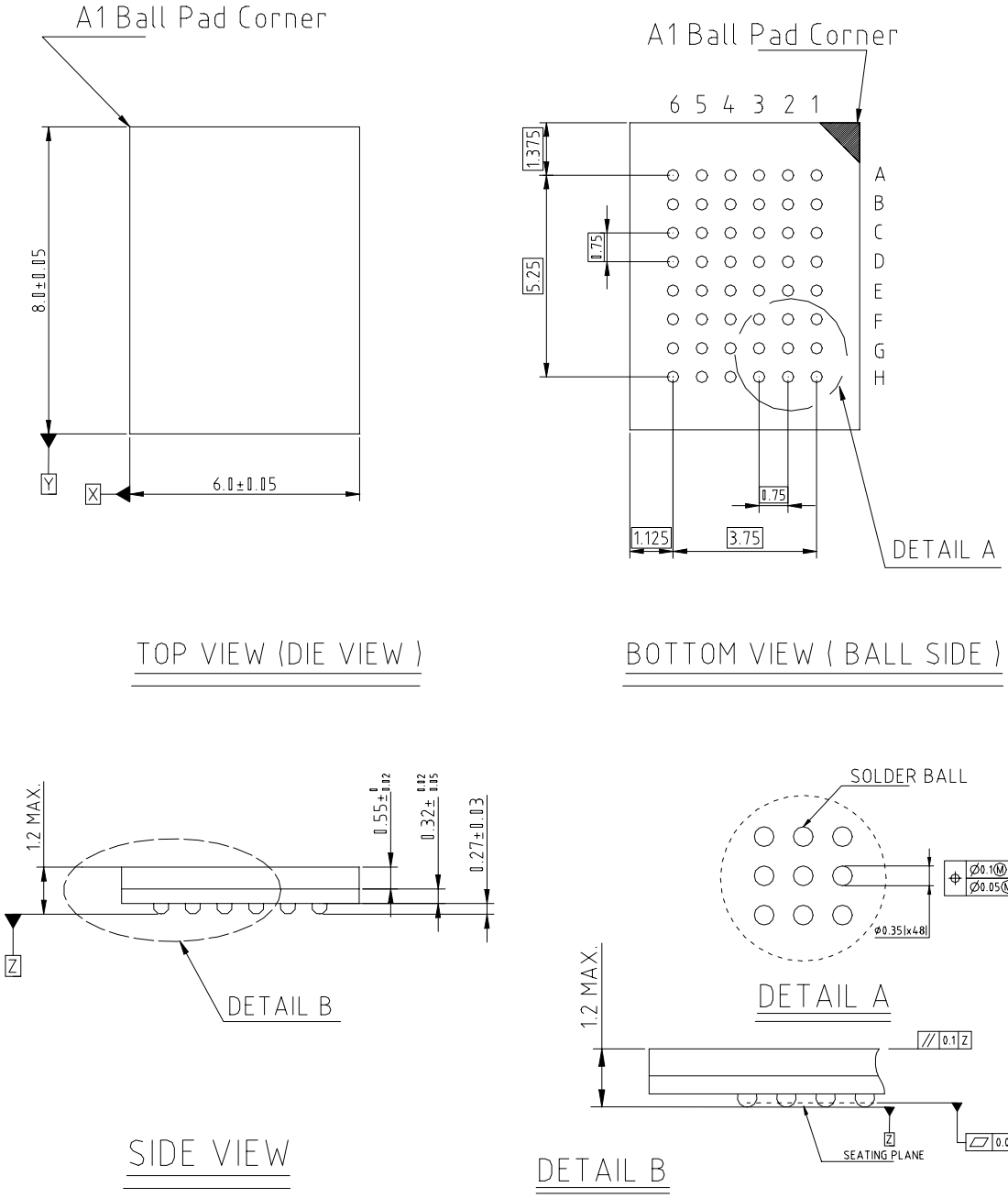




UNIT / SYMBOL	INCH(REF)	MM(BASE)
A	0.047(MAX)	1.20(MAX)
A1	0.004±0.002	0.10±0.05
A2	0.039±0.002	1.00±0.05
b	0.008±0.002	0.20±0.05
c	0.005(TYP)	0.127(TYP)
D	0.724±0.004	18.40±0.10
E	0.472±0.004	12.00±0.10
e	0.020(TYP)	0.50(TYP)
HD	0.787±0.008	20.00±0.20
L	0.0197±0.004	0.50±0.10
L1	0.0315±0.004	0.80±0.10
y	0.003(MAX)	0.076(MAX)
θ	0°~5°	0°~5°



48 ball 6.0mmX8.0mm TFBGA Package Outline Dimension



ORDERING INFORMATION

INDUSTRIAL TEMPERATURE

PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μA) typ.	PACKAGE
UT62L51316BS-55LI	55	20	48 BALL TFBGA
UT62L51316BS-55LLI	55	2	48 BALL TFBGA
UT62L51316BS-70LI	70	20	48 BALL TFBGA
UT62L51316BS-70LLI	70	2	48 BALL TFBGA
UT62L51316BS-100LI	100	20	48 BALL TFBGA
UT62L51316BS-100LLI	100	2	48 BALL TFBGA
UT62L51316LC-55LI	55	20	48 PIN TSOP-I
UT62L51316LC-55LLI	55	2	48 PIN TSOP-I
UT62L51316LC-70LI	70	20	48 PIN TSOP-I
UT62L51316LC-70LLI	70	2	48 PIN TSOP-I
UT62L51316LC-100LI	100	20	48 PIN TSOP-I
UT62L51316LC-100LLI	100	2	48 PIN TSOP-I

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